

# GUJARAT TECHNOLOGICAL UNIVERSITY

BE - SEMESTER– VI (New) EXAMINATION – WINTER 2019

**Subject Code: 2161101**
**Date: 11/12/2019**
**Subject Name: VLSI Technology & Design**
**Time: 02:30 PM TO 05:00 PM**
**Total Marks: 70**
**Instructions:**

1. Attempt all questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

		MARKS
<b>Q.1</b>	(a) Draw VLSI design flow with block diagram.	<b>03</b>
	(b) Differentiate between FPGA and CPLD	<b>04</b>
	(c) Discuss various packaging technology used for VLSI chips.	<b>07</b>
<b>Q.2</b>	(a) Explain the concept of MOSFET as a switch.	<b>03</b>
	(b) Justify that size of PMOS transistor chosen to be 2.5 times of an NMOS transistor.	<b>04</b>
	(c) Design a resistive load inverter with $R_L=1K\Omega$ , such that $V_{OL} = 0.6V$ . The enhancement type driver transistor has the following parameters: $V_{dd} = 5V$ , $V_{To} = 1V$ , $\gamma = 0.2 V^{1/2}$ , $\lambda = 0$ , $\mu_n C_{ox} = 22 \mu A/V^2$ . Determine i) Require aspect ratio. $W/L$ ii) $V_{IL}$ and $V_{IH}$ and iii) noise margin $NM_L$ and $NM_H$	<b>07</b>
	<b>OR</b>	
	(c) Draw the inverter circuit with depletion type nMOS load. Mention the operating regions of driver and load transistors for different input voltages. Derive the expression of critical voltages $V_{IL}, V_{OL}, V_{IH}, V_{OH}$ .	<b>07</b>
<b>Q.3</b>	(a) Define following Terms: (i) Threshold Voltage (ii) Noise Margin (iii) Propagation Delay	<b>03</b>
	(b) Explain: Substrate bias effect.	<b>04</b>
	(c) Explain the energy band diagram of MOS structure at surface inversion and derive the expression for the maximum possible depth of the depletion region.	<b>07</b>
	<b>OR</b>	
<b>Q.3</b>	(a) Draw CMOS Inverter circuit and voltage transfer characteristics. Mention different operating region of NMOS and PMOS on VTC.	<b>03</b>
	(b) Derive expression for frequency of oscillation for three stage ring oscillator circuit. Draw necessary circuit and waveforms.	<b>04</b>
	(c) Derive the expression of $\tau_{PHL}$ of a CMOS inverter using differential equation method.	<b>07</b>
<b>Q.4</b>	(a) Discuss the effect of Full scaling(constant-Field scaling) on: (i) $C_{ox}$ (ii) $I_D$	<b>03</b>
	(b) Derive $R_{eq}$ of all regions in CMOS Transmission gates	<b>04</b>
	(c) Implement and Describe CMOS clocked RS flip-flop.	<b>07</b>

- Q.4** (a) Draw two-input CMOS NOR and NAND gate circuits. **03**  
(b) Which are the four general criteria to measure design quality of a fabricated integrated circuit (chip)? Briefly explain each of them. **04**  
(c) Realize the following Boolean function using CMOS Transmission Gates. **07**  
 $F = AB + A'C' + AB'C$

- Q.5** (a) Draw the circuit diagram of domino CMOS logic gate. **03**  
(b) Explain Voltage bootstrapping. **04**  
(c) Implement and Describe CMOS clocked JK flip-flop. **07**

**OR**

- Q.5** (a) Draw general layout of an H-tree clock distribution network. **03**  
(b) Describe in brief : Built in Self Test (BIST) **04**  
(c) What is Latch up? Explain the prevention techniques. **07**

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